IEEE EDS Kansai Chapter IMFEDK Best Paper Award

Paper ID: C-3
Titled: “Demonstration of High Channel Mobility in 4H-SiC MOSFETs by Utilizing Phosphorus-Doped Gate Oxide”
Authors: Dai Okamoto, H. Yano, K. Hirata, S. Kotake, T. Hatayama, T. Fuyuki
Affiliation: Nara Institute of Science and Technology

IEEE EDS Kansai Chapter IMFEDK Student Paper Award

Author: Yosuke Tojo1, Paper ID: PA-4
Titled: “Location Controls of Crystallized Areas in Silicon Films Utilizing Cage Shape Protein”
Coauthors: A. Miura1,2, I. Yamashita1,3,4, Y. Uraoka1,4
Affiliation: 1Nara Institute of Science and Technology, 2National Chiao Tung University, 3Panasonic, 4CREST

Author: Hideo Shimizu, Paper ID: PA-12
Titled: “Reduction of self-heating effect in silicon MOSFETs on directly bonded Si-on-SiC wafer with high heat conductance ”
Coauthor: R. Araki, H. Shinohara, H. Kinoshita, M. Yoshimoto
Affiliation: Kyoto Institute of Technology

Author: Daishi Ino, Paper ID: PA-16
Titled: “Performance Evaluation of 1-V Deep Sub-micron Dynamic-Threshold SOI MOSFET”
Coauthors: T. Tochio, Y. Omura
Affiliation: Kansai University

Author: Yuta Goto, Paper ID: PB-4
Titled: “Chemical Bonding Features at TiO2/Pt Interface and Their Impact on Resistance-Switching Properties”
Coauthors: A. Ohta, H. Murakami, S. Higashi, S. Miyazaki
Affiliation: Hiroshima University

Author: Kumiho Tsuji, Paper ID: PC-4
Titled: “Micro-fabrication and characterization of an ion-sensitive ZnO-based transistor on a glass substrate”
Coauthors: K. Koike, K. Ogata, S. Sasa, M. Inoue, M. Yano
Affiliation: Osaka Institute of Technology